

N V Kryzhanovskaya

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

192
papers

1,284
citations

19
h-index

27
g-index

209
ext. papers

1,501
ext. citations

1.2
avg, IF

3.95
L-index

| # | Paper | IF | Citations |
|-----|--|------|-----------|
| 192 | On-chip light detection using integrated microdisk laser and photodetector bonded onto Si board. <i>Laser Physics Letters</i> , 2022 , 19, 016201 | 1.5 | 0 |
| 191 | Photoluminescence study of InP and In(As, P) inclusions into Si (100) substrate. <i>Journal of Physics: Conference Series</i> , 2022 , 2227, 012017 | 0.3 | |
| 190 | Dynamic characteristics and noise modelling of directly modulated quantum well-dots microdisk lasers on silicon. <i>Laser Physics Letters</i> , 2022 , 19, 025801 | 1.5 | |
| 189 | 1.3 fH optically-pumped monolithic VCSEL based on GaAs with InGa(Al)As superlattice active region. <i>Laser Physics Letters</i> , 2022 , 19, 075801 | 1.5 | 2 |
| 188 | Influence of dielectric overlayers on self-heating of a microdisk laser. <i>Journal of Physics: Conference Series</i> , 2021 , 2086, 012100 | 0.3 | |
| 187 | Quantum-dot microlasers based on whispering gallery mode resonators. <i>Light: Science and Applications</i> , 2021 , 10, 80 | 16.7 | 7 |
| 186 | Optical Properties of Three-Dimensional InGaP(As) Islands Formed by Substitution of Fifth-Group Elements. <i>Optics and Spectroscopy (English Translation of Optika I Spektroskopiya)</i> , 2021 , 129, 256-260 | 0.7 | |
| 185 | III-V microdisk/microring resonators and injection microlasers. <i>Journal Physics D: Applied Physics</i> , 2021 , 54, 453001 | 3 | 4 |
| 184 | Improved performance of InGaAs/GaAs microdisk lasers epi-side down bonded onto a silicon board. <i>Optics Letters</i> , 2021 , 46, 3853-3856 | 3 | 6 |
| 183 | Energy Consumption at High-Frequency Modulation of an Uncooled InGaAs/GaAs/AlGaAs Microdisk Laser. <i>Technical Physics Letters</i> , 2021 , 47, 685-688 | 0.7 | |
| 182 | Temperature stability of small-signal modulation response of WGM microlasers with InGaAs/GaAs quantum well-dots in the active region. <i>Journal of Physics: Conference Series</i> , 2021 , 2086, 012082 | 0.3 | |
| 181 | Output power of multilayered InGaAs/GaAs quantum well-dot microdisk lasers. <i>Journal of Physics: Conference Series</i> , 2021 , 2086, 012081 | 0.3 | 0 |
| 180 | Numerical simulation of optical coupling between a microring resonator and a directly connected straight waveguide. <i>Journal of Physics: Conference Series</i> , 2021 , 2086, 012162 | 0.3 | |
| 179 | Saturation Power of a Semiconductor Optical Amplifier Based on Self-Organized Quantum Dots. <i>Semiconductors</i> , 2021 , 55, S67-S71 | 0.7 | 0 |
| 178 | Lasing of Injection Microdisks with InAs/InGaAs/GaAs Quantum Dots Transferred to Silicon. <i>Technical Physics Letters</i> , 2020 , 46, 783-786 | 0.7 | 1 |
| 177 | Comparative Analysis of Injection Microdisk Lasers Based on InGaAsN Quantum Wells and InAs/InGaAs Quantum Dots. <i>Semiconductors</i> , 2020 , 54, 263-267 | 0.7 | 2 |
| 176 | Light Emitting Devices Based on Quantum Well-Dots. <i>Applied Sciences (Switzerland)</i> , 2020 , 10, 1038 | 2.6 | 20 |

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| 175 | Ultimate Lasing Temperature of Microdisk Lasers. <i>Semiconductors</i> , 2020 , 54, 677-681 | 0.7 | 2 |
| 174 | Strip-loaded horizontal slot waveguide for routing microdisk laser emission. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2020 , 37, 1878 | 1.7 | 2 |
| 173 | InAs/GaAs Quantum Dot Microlasers Formed on Silicon Using Monolithic and Hybrid Integration Methods. <i>Materials</i> , 2020 , 13, | 3.5 | 9 |
| 172 | Dielectric surrounding bleaches the optical bond between a microdisk resonator and a straight optical waveguide. <i>Journal of Physics: Conference Series</i> , 2020 , 1695, 012128 | 0.3 | 1 |
| 171 | Optical properties of InGaN/GaN QDs nanorods by top-down fabrication after KOH treatment. <i>Journal of Physics: Conference Series</i> , 2020 , 1695, 012046 | 0.3 | |
| 170 | Investigation of microdisk and microring lasers based on InGaAs/GaAs QWDs by the interferometry method. <i>Journal of Physics: Conference Series</i> , 2020 , 1695, 012093 | 0.3 | |
| 169 | Analysis of the lasing characteristics of InGaAs/GaAs WGM microlasers. <i>Journal of Physics: Conference Series</i> , 2020 , 1695, 012096 | 0.3 | |
| 168 | Experimental investigation of the far-field emission pattern of microdisk laser modes. <i>Journal of Physics: Conference Series</i> , 2020 , 1695, 012094 | 0.3 | |
| 167 | Structural and optical characterization of dilute phosphide planar heterostructures with high nitrogen content on silicon. <i>CrystEngComm</i> , 2020 , 22, 283-292 | 3.3 | 5 |
| 166 | Impact of Self-Heating and Elevated Temperature on Performance of Quantum Dot Microdisk Lasers. <i>IEEE Journal of Quantum Electronics</i> , 2020 , 56, 1-8 | 2 | 8 |
| 165 | Monolithic integration of InP on Si by molten alloy driven selective area epitaxial growth. <i>Nanoscale</i> , 2020 , 12, 23780-23788 | 7.7 | 1 |
| 164 | The Effect of Self-Heating on the Modulation Characteristics of a Microdisk Laser. <i>Technical Physics Letters</i> , 2020 , 46, 515-519 | 0.7 | 4 |
| 163 | A Study of the Photoresponse in Graphene Produced by Chemical Vapor Deposition. <i>Semiconductors</i> , 2020 , 54, 991-998 | 0.7 | |
| 162 | Synthesis of Morphologically Developed InGaN Nanostructures on Silicon: Influence of the Substrate Temperature on the Morphological and Optical Properties. <i>Semiconductors</i> , 2020 , 54, 1075-1077 | | 2 |
| 161 | A Micro Optocoupler Based on a Microdisk Laser and a Photodetector with an Active Region Based on Quantum Well-Dots. <i>Technical Physics Letters</i> , 2020 , 46, 629-632 | 0.7 | 0 |
| 160 | Energy Consumption for High-Frequency Switching of a Quantum-Dot Microdisk Laser. <i>Technical Physics Letters</i> , 2019 , 45, 847-849 | 0.7 | 3 |
| 159 | Evaluation of energy-to-data ratio of quantum-dot microdisk lasers under direct modulation. <i>Journal of Applied Physics</i> , 2019 , 126, 063107 | 2.5 | 10 |
| 158 | Silicon Nanopillar Microarrays: Formation and Resonance Reflection of Light. <i>Semiconductors</i> , 2019 , 53, 205-209 | 0.7 | 1 |

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| 157 | Dynamics of Broadband Lasing Cascade from a Single Dot-in-well InGaAs Microdisk. <i>Scientific Reports</i> , 2019 , 9, 5635 | 4.9 | 4 |
| 156 | Growth and Characterization of GaP/GaPAs Nanowire Heterostructures with Controllable Composition. <i>Physica Status Solidi - Rapid Research Letters</i> , 2019 , 13, 1900350 | 2.5 | 19 |
| 155 | Evaluation of the Impact of Surface Recombination in Microdisk Lasers by Means of High-Frequency Modulation. <i>Semiconductors</i> , 2019 , 53, 1099-1103 | 0.7 | 1 |
| 154 | High speed data transmission using directly modulated microdisk lasers based on InGaAs/GaAs quantum well-dots. <i>Optics Letters</i> , 2019 , 44, 5442-5445 | 3 | 14 |
| 153 | Direct modulation characteristics of microdisk lasers with InGaAs/GaAs quantum well-dots. <i>Photonics Research</i> , 2019 , 7, 664 | 6 | 16 |
| 152 | Lasing in III-V microdisk core/TiO ₂ shell lasers. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2019 , 36, 2285 | 1.7 | 3 |
| 151 | Specific Features of the Current-Voltage Characteristic of Microdisk Lasers Based on InGaAs/GaAs Quantum Well-Dots. <i>Technical Physics Letters</i> , 2019 , 45, 994-996 | 0.7 | 6 |
| 150 | Microlasers based on GaAs and Si. <i>Journal of Physics: Conference Series</i> , 2019 , 1410, 012001 | 0.3 | |
| 149 | Current induced mode competition in microdisk lasers. <i>Journal of Physics: Conference Series</i> , 2019 , 1410, 012117 | 0.3 | |
| 148 | Microdisk resonators as high-sensitive devices for biodetection. <i>Journal of Physics: Conference Series</i> , 2019 , 1410, 012178 | 0.3 | |
| 147 | InGaN nanostructures of a branched morphology on silicon substrate: MBE synthesis and properties. <i>Journal of Physics: Conference Series</i> , 2019 , 1410, 012052 | 0.3 | |
| 146 | Synthesis by Molecular Beam Epitaxy and Properties of InGaN Nanostructures of Branched Morphology on a Silicon Substrate. <i>Technical Physics Letters</i> , 2019 , 45, 1111-1113 | 0.7 | 4 |
| 145 | Record Low Threshold Current Density in Quantum Dot Microdisk Laser. <i>Semiconductors</i> , 2019 , 53, 1888-1890 | 1.9 | 6 |
| 144 | Investigation of optical properties of In(Ga)As/GaAs mesa structures with active region based on quantum wells, quantum dots, and quantum well-dots. <i>Journal of Physics: Conference Series</i> , 2019 , 1410, 012157 | 0.3 | 2 |
| 143 | The Use of Microdisk Lasers Based on InAs/InGaAs Quantum Dots in Biodetection. <i>Technical Physics Letters</i> , 2019 , 45, 1178-1181 | 0.7 | 2 |
| 142 | InGaN/GaN QDs nanorods for light emitters: Processing and properties 2019 , | | 1 |
| 141 | Resonance reflection of light by ordered silicon nanopillar arrays with the vertical p-n junction. <i>Thin Solid Films</i> , 2019 , 672, 109-113 | 2.2 | 4 |
| 140 | Coherent Growth of InP/InAsP/InP Nanowires on a Si (111) Surface by Molecular-Beam Epitaxy. <i>Technical Physics Letters</i> , 2018 , 44, 112-114 | 0.7 | 9 |

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| 139 | Elevated temperature lasing from injection microdisk lasers on silicon. <i>Laser Physics Letters</i> , 2018 , 15, 015802 | 1.5 | 13 |
| 138 | InGaN/GaN QDs Nanorods: Processing and Properties. <i>Semiconductors</i> , 2018 , 52, 2096-2098 | 0.7 | |
| 137 | Injection microdisk lasers based on multilayers of InGaAs/GaAs quantum well-dot structures. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 041002 | 0.3 | |
| 136 | Structural properties of multilayer heterostructure for quantum-cascade lasers grown by MBE growth. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 022005 | 0.3 | |
| 135 | Study of p-type contact topography influence on characteristics of microdisk and microring lasers. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 041012 | 0.3 | 2 |
| 134 | A novel approach to characterization of bottom sub-cell in multijunction solar cell using photoluminescence.. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 041039 | 0.3 | |
| 133 | Room temperature lasing from microdisk laser in aqueous medium. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 051007 | 0.3 | 5 |
| 132 | Room temperature lasing in injection microdisks with InGaAsN/GaAs quantum well active region. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 081048 | 0.3 | 1 |
| 131 | Violation of Local Electroneutrality in the Quantum Well of a Semiconductor Laser with Asymmetric Barrier Layers. <i>Semiconductors</i> , 2018 , 52, 1621-1629 | 0.7 | 3 |
| 130 | Dielectric surrounding decimates eigenmodes of microdisk optical resonators. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 051031 | 0.3 | 2 |
| 129 | Influence of coating layers on characteristics of microdisk lasers with InAs/InGaAs quantum dots active region. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 041020 | 0.3 | |
| 128 | Enhanced light outcoupling in microdisk lasers via Si spherical nanoantennas. <i>Journal of Applied Physics</i> , 2018 , 124, 163102 | 2.5 | 13 |
| 127 | Phosphorus-Based Nanowires Grown by Molecular-Beam Epitaxy on Silicon. <i>Semiconductors</i> , 2018 , 52, 1416-1419 | 0.7 | 2 |
| 126 | Highly efficient injection microdisk lasers based on quantum well-dots. <i>Optics Letters</i> , 2018 , 43, 4554-4557 | | 39 |
| 125 | Edge-emitting and microdisk lasers based on hybrid quantum-well-dot structures 2018 , | | 1 |
| 124 | Reflection Spectra of Microarrays of Silicon Nanopillars. <i>Optics and Spectroscopy (English Translation of Optika I Spektroskopiya)</i> , 2018 , 124, 730-734 | 0.7 | 2 |
| 123 | 3.5- μm radius race-track microlasers operating at room temperature with 1.3- μm quantum dot active region. <i>Journal of Applied Physics</i> , 2017 , 121, 043104 | 2.5 | 5 |
| 122 | Specific features of waveguide recombination in laser structures with asymmetric barrier layers. <i>Semiconductors</i> , 2017 , 51, 254-259 | 0.7 | 2 |

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| 121 | Light Outcoupling from Quantum Dot-Based Microdisk Laser via Plasmonic Nanoantenna. <i>ACS Photonics</i> , 2017 , 4, 275-281 | 6.3 | 27 |
| 120 | Study of the structural and optical properties of GaP(N) layers synthesized by molecular-beam epitaxy on Si(100) 4 \times 4 substrates. <i>Semiconductors</i> , 2017 , 51, 267-271 | 0.7 | 2 |
| 119 | Light absorption by an atomic force microscope probe. <i>Journal of Physics: Conference Series</i> , 2017 , 816, 012036 | 0.3 | |
| 118 | Lasing of metamorphic hybrid 1300nm spectral band VCSEL under optical pumping up to 120 $^{\circ}$ C 2017 , | | 2 |
| 117 | On the high characteristic temperature of an InAs/GaAs/InGaAsP QD laser with an emission wavelength of \sim 1.5 μ m on an InP substrate. <i>Semiconductors</i> , 2017 , 51, 1332-1336 | 0.7 | 3 |
| 116 | InAs quantum dots grown by MOCVD in GaAs and metamorphic InGaAs matrixes. <i>Journal of Physics: Conference Series</i> , 2017 , 816, 012024 | 0.3 | 1 |
| 115 | Heat-sink free CW operation of injection microdisk lasers grown on Si substrate with emission wavelength beyond 1.3 μ m. <i>Optics Letters</i> , 2017 , 42, 3319-3322 | 3 | 33 |
| 114 | Investigation of lasers based on coupled waveguides by near-field scanning optical microscopy. <i>Journal of Physics: Conference Series</i> , 2017 , 929, 012070 | 0.3 | |
| 113 | Optical properties of metamorphic hybrid heterostructures for vertical-cavity surface-emitting lasers operating in the 1300-nm spectral range. <i>Semiconductors</i> , 2017 , 51, 1127-1132 | 0.7 | 2 |
| 112 | Near-field mapping of three-particle plasmonic structures. <i>Journal of Physics: Conference Series</i> , 2017 , 917, 062012 | 0.3 | |
| 111 | Investigation of the effect of surface passivation on microdisk lasers based on InGaAsN/GaAs quantum well active region. <i>Journal of Physics: Conference Series</i> , 2017 , 917, 052002 | 0.3 | 1 |
| 110 | Epitaxial growth and investigation of GaP/GaP(As)N heterostructures on Si (100) 4 \times 4 substrates. <i>Journal of Physics: Conference Series</i> , 2017 , 917, 032044 | 0.3 | 1 |
| 109 | Investigation of whispering gallery modes in microlasers by scanning near-field optical microscopy. <i>Journal of Physics: Conference Series</i> , 2017 , 917, 052036 | 0.3 | 1 |
| 108 | Electrically pumped InGaAs/GaAs quantum well microdisk lasers directly grown on Si(100) with Ge/GaAs buffer. <i>Optics Express</i> , 2017 , 25, 16754-16760 | 3.3 | 12 |
| 107 | MBE growth, structural and optical properties of multilayer heterostructures for quantum-cascade lasers. <i>Journal of Physics: Conference Series</i> , 2017 , 917, 052012 | 0.3 | 2 |
| 106 | Laser generation at 1.3 μ m in vertical microcavities containing InAs/InGaAs quantum dot arrays under optical pumping. <i>Technical Physics Letters</i> , 2016 , 42, 1009-1012 | 0.7 | 3 |
| 105 | Laser characteristics of an injection microdisk with quantum dots and its free-space outcoupling efficiency. <i>Semiconductors</i> , 2016 , 50, 1408-1411 | 0.7 | 5 |
| 104 | Electrically pumped microdisk lasers with semitransparent conducting pyrolytic carbon film. <i>Journal of Physics: Conference Series</i> , 2016 , 741, 012076 | 0.3 | |

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| 103 | Improved emission outcoupling from microdisk laser by Si nanospheres. <i>Journal of Physics: Conference Series</i> , 2016 , 741, 012158 | 0.3 | 2 |
| 102 | High-temperature lasing in diode microdisk lasers with InAs/InGaAs quantum dots. <i>Journal of Physics: Conference Series</i> , 2016 , 769, 012056 | 0.3 | 1 |
| 101 | Lasers with asymmetric barrier layers: A promising type of injection lasers. <i>Journal of Physics: Conference Series</i> , 2016 , 741, 012111 | 0.3 | 1 |
| 100 | Compact microdisk cavity laser with GaInNAs/GaAs quantum well. <i>Journal of Physics: Conference Series</i> , 2016 , 741, 012110 | 0.3 | |
| 99 | Microdisk lasers based on GaInNAs(Sb)/GaAs(N) quantum wells. <i>Journal of Applied Physics</i> , 2016 , 120, 233103 | 2.5 | 6 |
| 98 | Multilayer heterostructures for quantum-cascade lasers operating in the terahertz frequency range. <i>Semiconductors</i> , 2016 , 50, 662-666 | 0.7 | 7 |
| 97 | Microdisk Injection Lasers for the 1.27- μm Spectral Range. <i>Semiconductors</i> , 2016 , 50, 390-393 | 0.7 | 12 |
| 96 | Theory of the power characteristics of quantum-well lasers with asymmetric barrier layers: Inclusion of asymmetry in electron- and hole-state filling. <i>Semiconductors</i> , 2016 , 50, 1362-1368 | 0.7 | 7 |
| 95 | The effect of sulfide passivation on luminescence from microdisks with quantum wells and quantum dots. <i>Technical Physics Letters</i> , 2015 , 41, 654-657 | 0.7 | 3 |
| 94 | Optical and electrical properties of silicon nanopillars. <i>Semiconductors</i> , 2015 , 49, 939-943 | 0.7 | 4 |
| 93 | The effect of asymmetric barrier layers in the waveguide region on power characteristics of QW lasers. <i>Technical Physics Letters</i> , 2015 , 41, 439-442 | 0.7 | 6 |
| 92 | Room Temperature Lasing in 1- μm Microdisk Quantum Dot Lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2015 , 21, 709-713 | 3.8 | 22 |
| 91 | Thermal resistance of ultra-small-diameter disk microlasers. <i>Semiconductors</i> , 2015 , 49, 674-678 | 0.7 | 7 |
| 90 | Observation of zero linewidth enhancement factor at excited state band in quantum dot laser. <i>Electronics Letters</i> , 2015 , 51, 1686-1688 | 1.1 | 10 |
| 89 | Continuous-wave lasing at 100 $^{\circ}\text{C}$ in 1.3 μm quantum dot microdisk diode laser. <i>Electronics Letters</i> , 2015 , 51, 1354-1355 | 1.1 | 29 |
| 88 | Mode selection in InAs quantum dot microdisk lasers using focused ion beam technique. <i>Optics Letters</i> , 2015 , 40, 4022-5 | 3 | 13 |
| 87 | Suppression of sublinearity of light-current curve in 850 μm quantum well laser with asymmetric barrier layers. <i>Electronics Letters</i> , 2015 , 51, 1106-1108 | 1.1 | 9 |
| 86 | Modeling, synthesis and study of highly efficient solar cells based on III-nitride nanowire arrays grown on Si substrates. <i>Journal of Physics: Conference Series</i> , 2015 , 643, 012115 | 0.3 | 10 |

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| 85 | The effect of the sulfide passivation on the luminescence of microdisk mesas with quantum wells and quantum dots. <i>Journal of Physics: Conference Series</i> , 2015 , 643, 012043 | 0.3 | 1 |
| 84 | MBE growth and optical properties of GaAs nanowires grown on Si(111) substrate using two-temperature steps regime. <i>Journal of Physics: Conference Series</i> , 2015 , 643, 012003 | 0.3 | |
| 83 | Room temperature continuous wave operation of injection quantum dot microdisk lasers. <i>Journal of Physics: Conference Series</i> , 2015 , 643, 012002 | 0.3 | 1 |
| 82 | On the optimization of asymmetric barrier layers in InAlGaAs/AlGaAs laser heterostructures on GaAs substrates. <i>Semiconductors</i> , 2015 , 49, 935-938 | 0.7 | 7 |
| 81 | Microdisk lasers based on GaInNAsSb/GaAsN quantum well active region. <i>Journal of Physics: Conference Series</i> , 2015 , 643, 012040 | 0.3 | 0 |
| 80 | Single-Mode Emission From 49-nm Microdisk Lasers With Dense Array of InGaAs Quantum Dots. <i>Journal of Lightwave Technology</i> , 2015 , 33, 171-175 | 4 | 8 |
| 79 | Crystallographic dependent in-situ CBr ₄ selective nano-area etching and local regrowth of InP/InGaAs by MOVPE. <i>Journal of Crystal Growth</i> , 2014 , 406, 111-115 | 1.6 | 4 |
| 78 | Whispering-gallery mode microcavity quantum-dot lasers. <i>Quantum Electronics</i> , 2014 , 44, 189-200 | 1.8 | 24 |
| 77 | Lasing in microdisk resonators with InAs/InGaAs quantum dots transferred on a silicon substrate. <i>Journal of Physics: Conference Series</i> , 2014 , 541, 012049 | 0.3 | 3 |
| 76 | Ultrasmall microdisk and microring lasers based on InAs/InGaAs/GaAs quantum dots. <i>Nanoscale Research Letters</i> , 2014 , 9, 3266 | 5 | 34 |
| 75 | Control of emission spectra in quantum dot microdisk/microring lasers. <i>Optics Express</i> , 2014 , 22, 25782-73.3 | 3.3 | 14 |
| 74 | Lasing in microdisks of ultrasmall diameter. <i>Semiconductors</i> , 2014 , 48, 1626-1630 | 0.7 | 7 |
| 73 | Spectral dependence of the linewidth enhancement factor in quantum dot lasers. <i>Semiconductors</i> , 2013 , 47, 1656-1660 | 0.7 | 1 |
| 72 | Room-temperature lasing in microring cavities with an InAs/InGaAs quantum-dot active region. <i>Semiconductors</i> , 2013 , 47, 1387-1390 | 0.7 | 7 |
| 71 | Laser generation in microdisc resonators with InAs/GaAs quantum dots transferred on a silicon substrate. <i>Technical Physics Letters</i> , 2013 , 39, 830-833 | 0.7 | 4 |
| 70 | Optimization of the design and mode of operation of a QD laser for reducing the heat-to-bitrate ratio. <i>Semiconductors</i> , 2013 , 47, 1097-1102 | 0.7 | |
| 69 | Light-current characteristic of a quantum well laser with asymmetric barrier layers. <i>Journal of Applied Physics</i> , 2013 , 114, 143103 | 2.5 | 10 |
| 68 | Optical properties of GaN _x As _y P _{1-x-y} semiconductor quaternary solid solutions. <i>Journal of Surface Investigation</i> , 2012 , 6, 479-481 | 0.5 | 1 |

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| 67 | Effect of an excited-state optical transition on the linewidth enhancement factor of quantum dot lasers. <i>Semiconductors</i> , 2012 , 46, 225-230 | 0.7 | 4 |
| 66 | Improvement of temperature-stability in a quantum well laser with asymmetric barrier layers. <i>Applied Physics Letters</i> , 2012 , 100, 021107 | 3.4 | 22 |
| 65 | Quantum dot lasers and relevant nanoheterostructures 2012 , | | 7 |
| 64 | Effect of asymmetric barrier layers in the waveguide region on the temperature characteristics of quantum-well lasers. <i>Semiconductors</i> , 2012 , 46, 1027-1031 | 0.7 | 6 |
| 63 | High-temperature lasing in a microring laser with an active region based on InAs/InGaAs quantum dots. <i>Semiconductors</i> , 2012 , 46, 1040-1043 | 0.7 | 9 |
| 62 | Electroluminescence of GaP x N y As _{1-x-y} nanoheterostructures through a transparent electrode made of CVD graphene. <i>Semiconductors</i> , 2012 , 46, 796-800 | 0.7 | 8 |
| 61 | Semiconductor lasers with asymmetric barrier layers: An approach to high temperature stability. <i>Semiconductors</i> , 2011 , 45, 530-535 | 0.7 | 10 |
| 60 | Effect of AlGaAs-(AlGa) x O y pedestal parameters on characteristics of a microdisk laser with active region based on InAs/InGaAs quantum dots. <i>Semiconductors</i> , 2011 , 45, 962-965 | 0.7 | 1 |
| 59 | Effect of the nonlinear saturation of the gain on the peak modulation frequency in lasers based on self-assembled quantum dots. <i>Semiconductors</i> , 2011 , 45, 966-970 | 0.7 | 3 |
| 58 | Optical properties of quantum-confined heterostructures based on GaP x N y As _{1-x-y} alloys. <i>Semiconductors</i> , 2011 , 45, 1164-1168 | 0.7 | 8 |
| 57 | Bandedge-engineered quantum well laser. <i>Semiconductor Science and Technology</i> , 2011 , 26, 055025 | 1.8 | 18 |
| 56 | InGaN/GaN short-period superlattices: synthesis, properties, applications. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2308-2310 | | 2 |
| 55 | Single quantum well deep-green LEDs with buried InGaN/GaN short-period superlattice. <i>Journal of Crystal Growth</i> , 2011 , 315, 267-271 | 1.6 | 27 |
| 54 | A monolithic white LED with an active region based on InGaN QWs separated by short-period InGaN/GaN superlattices. <i>Semiconductors</i> , 2010 , 44, 808-811 | 0.7 | 12 |
| 53 | Optical and structural properties of InGaN/GaN short-period superlattices for the active region of light-emitting diodes. <i>Semiconductors</i> , 2010 , 44, 828-834 | 0.7 | 6 |
| 52 | Optical properties of quaternary GaN x As y P _{1-x-y} semiconductor alloys. <i>Semiconductors</i> , 2010 , 44, 857-860 | 0.7 | 5 |
| 51 | Structural and optical properties of InAlN/GaN distributed Bragg reflectors. <i>Semiconductors</i> , 2010 , 44, 949-953 | 0.7 | 3 |
| 50 | Formation of composite InGaN/GaN/InAlN quantum dots. <i>Semiconductors</i> , 2010 , 44, 1338-1341 | 0.7 | 2 |

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|----|--|-----|----|
| 49 | A 1.33 μm InAs/GaAs quantum dot laser with a 46 cm^{-1} modal gain. <i>Semiconductor Science and Technology</i> , 2008 , 23, 105004 | 1.8 | 36 |
| 48 | Molecular beam epitaxy growth methods of wavelength control for InAs/(In)GaAsN/GaAs heterostructures. <i>Nanotechnology</i> , 2008 , 19, 445715 | 3.4 | 6 |
| 47 | High-gain injection quantum-dot lasers operating at wavelengths above 1300 nm. <i>Technical Physics Letters</i> , 2008 , 34, 1008-1010 | 0.7 | 2 |
| 46 | Methods of controlling the emission wavelength in InAs/GaAsN/InGaAsN heterostructures on GaAs substrates. <i>Semiconductors</i> , 2008 , 42, 805-812 | 0.7 | 6 |
| 45 | Optical properties of strain-compensated InAs/InGaAsN/GaAsN superlattices. <i>Technical Physics Letters</i> , 2007 , 33, 384-387 | 0.7 | 1 |
| 44 | Metamorphic InAs quantum dots: Photoluminescence features related to cooperative phenomena in the quantum dot-matrix system. <i>Technical Physics Letters</i> , 2007 , 33, 590-593 | 0.7 | |
| 43 | Broad-area InAs/GaAs quantum dot lasers incorporating Intermixed passive waveguide. <i>Electronics Letters</i> , 2007 , 43, 29 | 1.1 | 4 |
| 42 | Metamorphic 1.5 μm -range quantum dot lasers on a GaAs substrate. <i>Semiconductor Science and Technology</i> , 2006 , 21, 691-696 | 1.8 | 26 |
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